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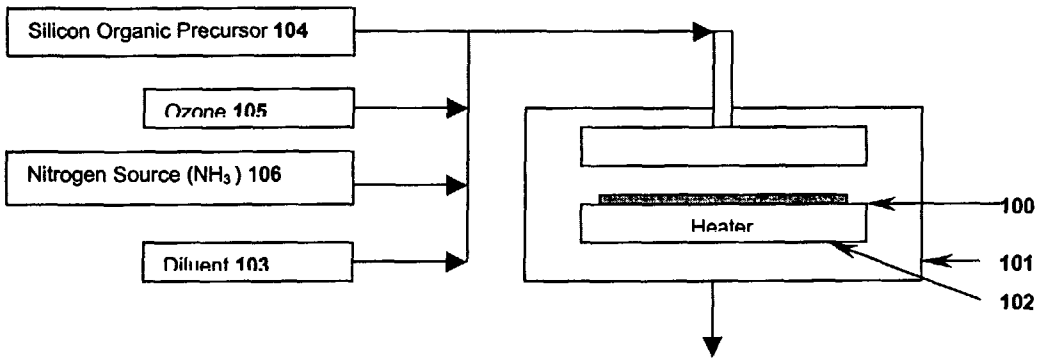
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(54) Title: LOW TERMPERATURE DEPOSITION OF SILICON OXIDES AND OXYNITRIDES



(57) Abstract: The present invention relates to low temperature (i.e., less than about 450 °C) chemical vapor deposition (CVD) and low temperature atomic layer deposition (ALD) processes for forming silicon oxide and/or silicon oxynitride derived from silicon organic precursors and ozone. The processes of the invention provide good step coverage. The invention can be utilized to deposit both high-k and low-k dielectrics.

WO 2004/017383 A2